

# MS1076

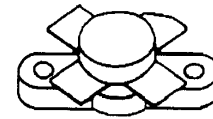
## RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

### Features

- 30 MHz
- 28 VOLTS
- GOLD METALLIZATION
- $P_{OUT} = 220$  W PEP
- $G_P = 12$  dB GAIN MINIMUM
- COMMON EMITTER CONFIGURATION

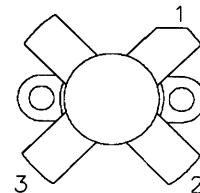
### DESCRIPTION:

The MS1076 is a 28 volt epitaxial NPN silicon planar transistor designed primarily for SSB and VHF communications. This device utilizes an emitter ballasted die geometry for maximum ruggedness and reliability.



.500 4LFL (M174)  
epoxy sealed

#### PIN CONNECTION



1. Collector      3. Base  
2. Emitter      4. Emitter

### ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector - Base Voltage	70	V
$V_{CEO}$	Collector - Emitter Voltage	35	V
$V_{EBO}$	Emitter - Base Voltage	4.0	V
$I_C$	Device Current	16	A
$P_{DISS}$	Power Dissipation	320	W
$T_J$	Junction Temperature	+200	°C
$T_{STG}$	Storage Temperature	- 65 to +150	°C

### Thermal Data

$R_{TH(J-C)}$	Junction - Case Thermal Resistance	0.7	°C/W
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## ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

### STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
<b>BV<sub>CES</sub></b>	<b>I<sub>C</sub> = 100 mA      V<sub>BE</sub> = 0 V</b>	<b>70</b>	---	---	<b>V</b>
<b>BV<sub>CEO</sub></b>	<b>I<sub>C</sub> = 200 mA      I<sub>B</sub> = 0 mA</b>	<b>35</b>	---	---	<b>V</b>
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 20 mA      I<sub>C</sub> = 0 mA</b>	<b>4.0</b>	---	---	<b>V</b>
<b>I<sub>CEO</sub></b>	<b>V<sub>CE</sub> = 30 V      I<sub>E</sub> = 0 mA</b>	---	---	<b>5</b>	<b>mA</b>
<b>I<sub>CES</sub></b>	<b>V<sub>CE</sub> = 35 V      I<sub>E</sub> = 0 mA</b>	---	---	<b>5</b>	<b>mA</b>
<b>H<sub>FE</sub></b>	<b>V<sub>CE</sub> = 5 V      I<sub>C</sub> = 7 A</b>	<b>15</b>	---	<b>50</b>	---

### DYNAMIC

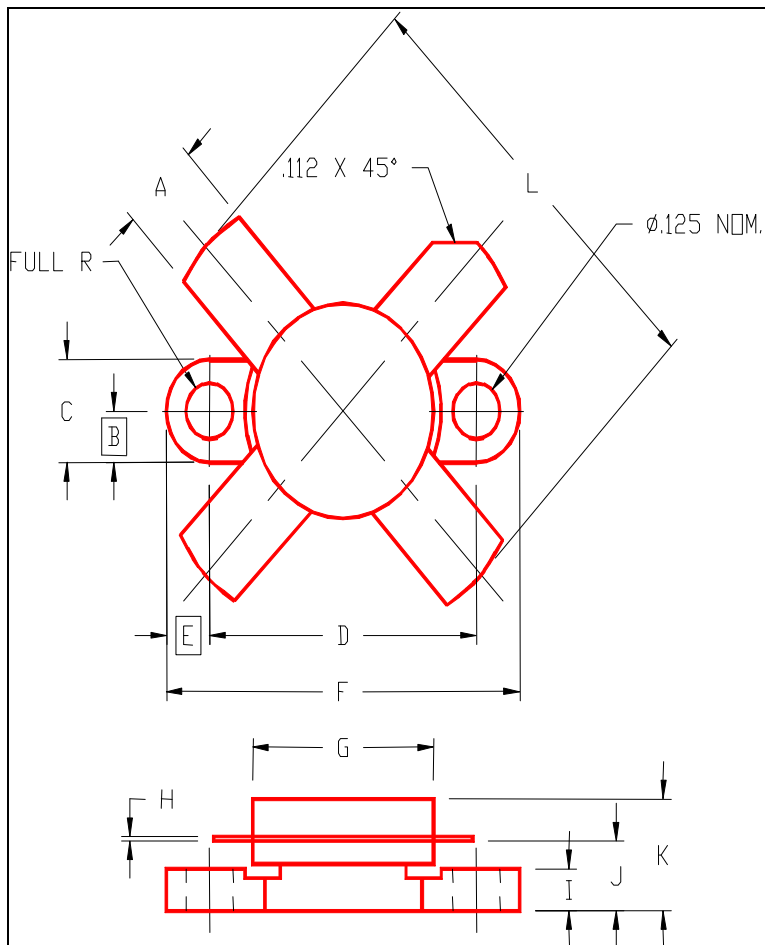
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 30 MHz      V<sub>CE</sub> = 28 V      I<sub>CQ</sub> = 750 mA</b>	<b>220</b>	---	---	<b>WPEP</b>
<b>G<sub>P</sub></b>	<b>f = 30 MHz      V<sub>CE</sub> = 28 V      I<sub>CQ</sub> = 750 mA</b>	<b>12</b>	---	---	<b>dB</b>
<b>η<sub>C</sub></b>	<b>f = 30 MHz      V<sub>CE</sub> = 28 V      I<sub>CQ</sub> = 750 mA</b>	<b>40</b>	---	---	<b>%</b>
<b>IMD</b>	<b>f = 30 MHz      V<sub>CE</sub> = 28 V      I<sub>CQ</sub> = 750 mA</b>	---	---	<b>-30</b>	<b>dBc</b>
<b>C<sub>OB</sub></b>	<b>f = 1 MHz      V<sub>CB</sub> = 28 V</b>	---	<b>450</b>	---	<b>pf</b>

Conditions:      f<sub>1</sub> = 30.000 MHz      f<sub>2</sub> = 30.001 MHz

### IMPEDANCE DATA

FREQ	Z <sub>IN</sub>	Z <sub>CL</sub>
<b>30 MHz</b>	<b>1.2 + j0.41</b>	<b>1.25 + j1.92</b>

**PACKAGE MECHANICAL DATA**



**PACKAGE STYLE M174**

	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.220/5,59	.230/5,84	I	.090/2,29	.110/2,79
B	.125/3,18		J	.160/4,06	.175/4,45
C	.245/6,22	.255/6,48	K		.280/7,11
D	.720/18,28	.730/18,54	L		1.050/26,67
E	.125/3,18				
F	.970/24,64	.980/24,89			
G	.495/12,57	.505/12,83			
H	.003/0,08	.007/0,18			